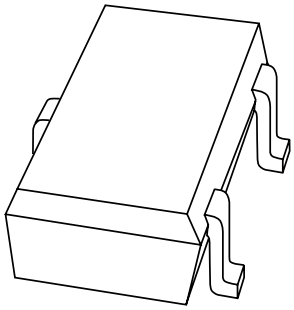
DATA SHEET



PMST4403
PNP switching transistor

Product data sheet
Supersedes data of 1997 May 29

1999 Apr 22

PNP switching transistor PMST4403

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- Switching and linear amplification.

DESCRIPTION

PNP switching transistor in a SOT323 plastic package.
NPN complement: PMST4401.

MARKING

TYPE NUMBER	MARKING CODE(1)
PMST4403	∗2T

Note

1. ∗ = - : Made in Hong Kong.
   ∗ = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

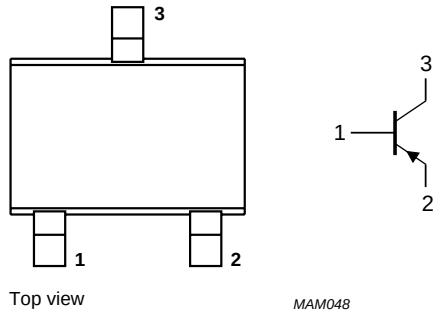


Fig.1 Simplified outline (SOT323) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	−40	V
V_{CEO}	collector-emitter voltage	open base	–	−40	V
V_{EBO}	emitter-base voltage	open collector	–	−5	V
I_C	collector current (DC)		–	−600	mA
I_{CM}	peak collector current		–	−800	mA
I_{BM}	peak base current		–	−200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	200	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = −40 V	−	−50	nA
		I_E = 0; V_{CB} = −40 V; T_j = 150 °C	−	−10	μA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = −5 V	−	−50	nA
h_{FE}	DC current gain	V_{CE} = −1 V; (see Fig.2)	−	−	
		I_C = −0.1 mA	30	−	
		I_C = −1 mA	60	−	
		I_C = −10 mA	100	−	
	DC current gain	I_C = −150 mA; V_{CE} = −2 V; note 1	100	300	
		I_C = −500 mA; V_{CE} = −2 V; note 1	20	−	
V_{CEsat}	collector-emitter saturation voltage	I_C = −150 mA; I_B = −15 mA; note 1	−	−400	mV
		I_C = −500 mA; I_B = −50 mA; note 1	−	−750	mV
V_{BEsat}	base-emitter saturation voltage	I_C = −150 mA: I_B = −15 mA; note 1	+750	−950	mV
		I_C = −500 mA; I_B = −50 mA; note 1	−	−1.3	V
C_c	collector capacitance	I_E = i_e = 0; V_{CB} = −10 V; f = 1 MHz	−	8.5	pF
C_e	emitter capacitance	I_C = i_c = 0; V_{EB} = −500 mV; f = 1 MHz	−	35	pF
f_T	transition frequency	I_C = −20 mA; V_{CE} = −10 V; f = 100 MHz	200	−	MHz
Switching times (between 10% and 90% levels); (see Fig.3)					
t_{on}	turn-on time	I_{Con} = −150 mA; I_{Bon} = −15 mA; I_{Boff} = 15 mA	−	40	ns
t_d	delay time		−	15	ns
t_r	rise time		−	30	ns
t_{off}	turn-off time		−	350	ns
t_s	storage time		−	300	ns
t_f	fall time		−	50	ns

Note

1. Pulse test: $t_p \leq 300\ \mu s$; $\delta \leq 0.02$.

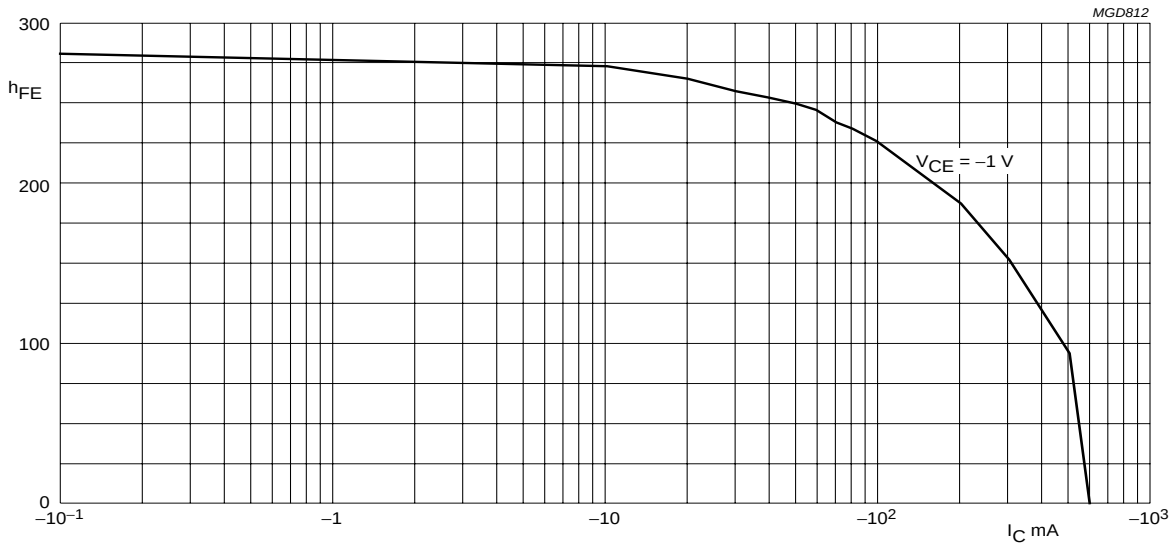
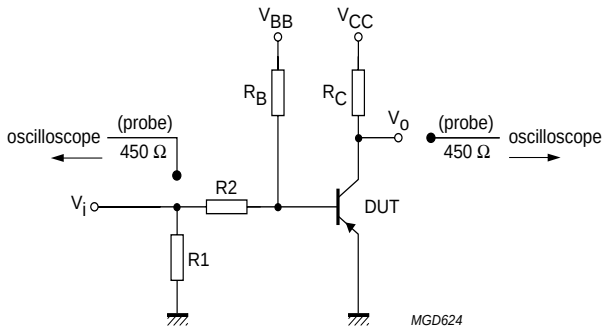


Fig.2 DC current gain; typical values.

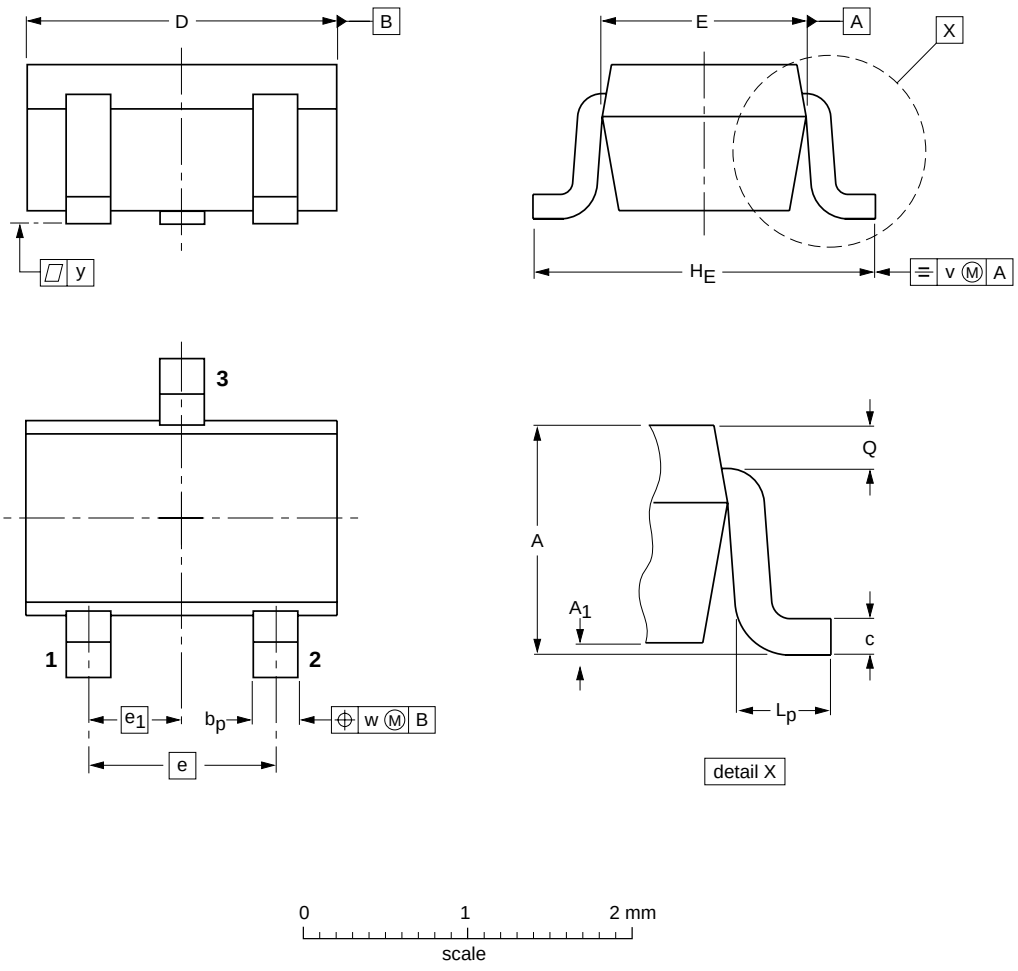


V_i = −9.5 V; T = 500 μs; t_p = 10 μs; $t_r = t_f \leq 3$ ns.
R1 = 68 Ω; R2 = 325 Ω; R_B = 325 Ω; R_C = 160 Ω.
V_{BB} = 3.5 V; V_{CC} = −29.5 V.
Oscilloscope input impedance Z_i = 50 Ω.

Fig.3 Test circuit for switching times.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT323**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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